

Gate resistor installed Dual N-channel MOSFET

KFC4B22270L Data Sheet

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1. GENERAL DESCRIPTION

Gate resistor installed Dual N-channel MOSFET
For lithium-ion secondary battery protection circuits

2. FEATURES

- Low source-source ON resistance: $R_{SS} (on)$ typ. = $18 \text{ m}\Omega$ ($V_{GS} = 3.8 \text{ V}$)
- CSP (Chip Size Package)
- RoHS compliant (EU RoHS / UL-94 V-0 / MSL: Level 1)

3. MARKING SYMBOL: 2J

4. PACKAGING

Embossed type (Thermo-compression sealing): 20,000 pcs / reel (standard)

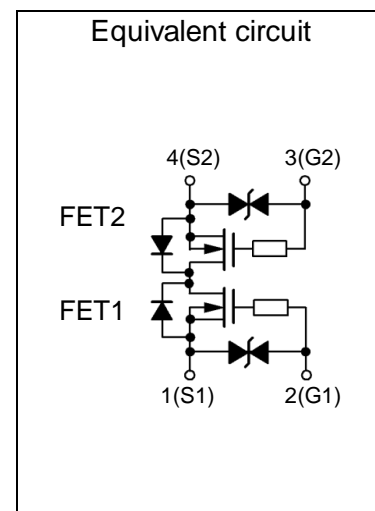
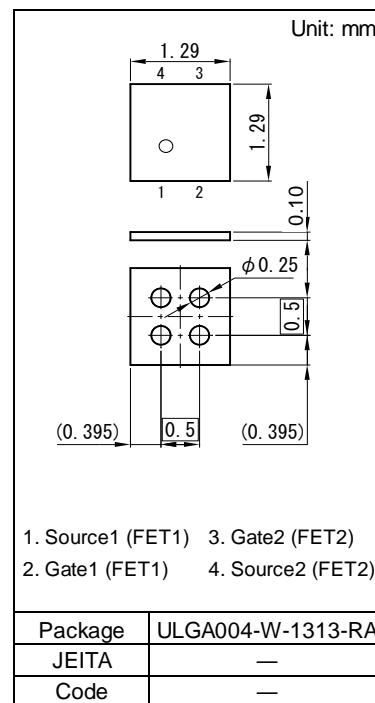
5. ABSOLUTE MAXIMUM RATINGS $T_a = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Source-source Voltage		VSS	20	V
Gate-source Voltage		VGS	±12	V
Source Current	DC	IS1 ^{*1}	4	A
		IS2 ^{*2}	8	
	Pulsed	ISp ^{*3}	40	
Total Power Dissipation	DC	PD1 ^{*1}	0.37	W
		PD2 ^{*2}	1.5	
Channel Temperature		Tch	150	°C
Storage Temperature Range		Tstg	-55 to +150	°C

6. THERMAL CHARACTERISTICS $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Thermal Resistance (ch-a)	Rth1 *1	338	$^\circ\text{C} / \text{W}$
	Rth2 *2	83	

- Note *1 Mounted on FR4 board (25.4 mm x 25.4 mm x t1.0 mm) using the minimum recommended pad size (36 μm Copper).
 *2 Mounted on Ceramic substrate (70 mm x 70 mm x t1.0 mm).
 *3 $t = 10 \mu\text{s}$, Duty Cycle $\leq 1\%$



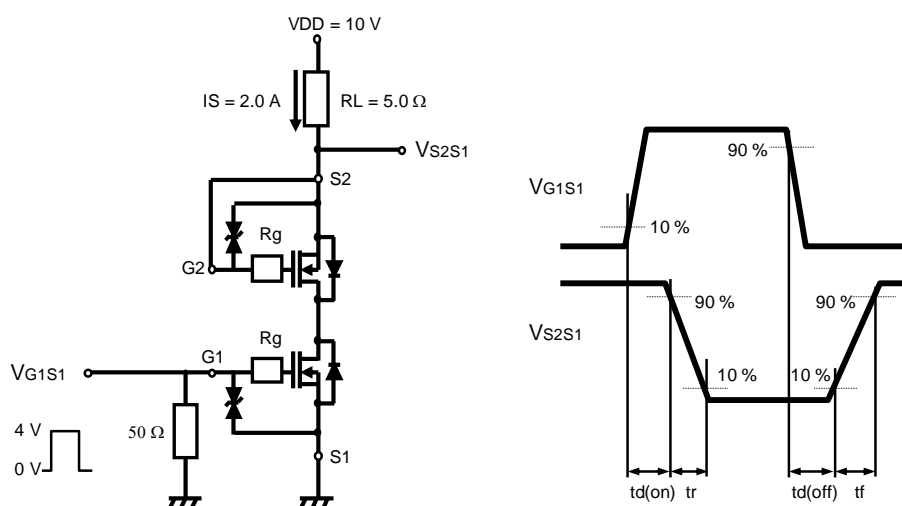
7. ELECTRICAL CHARACTERISTICS $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Source-source Breakdown Voltage	VSSS	$I_S = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	20			V
Zero Gate Voltage Source Current	ISSS	$V_{SS} = 20\text{ V}$, $V_{GS} = 0\text{ V}$			1.0	μA
Gate-source Leakage Current	IGSS	$V_{GS} = \pm 8\text{ V}$, $V_{SS} = 0\text{ V}$			± 10	μA
Gate-source Threshold Voltage	V_{th}	$I_S = 0.31\text{ mA}$, $V_{SS} = 10\text{ V}$	0.35	0.90	1.40	V
Source-source On-state Resistance	RSS(on)1	$I_S = 2.0\text{ A}$, $V_{GS} = 4.5\text{ V}$	12.0	17.0	22.0	$\text{m}\Omega$
	RSS(on)2	$I_S = 2.0\text{ A}$, $V_{GS} = 3.8\text{ V}$	12.5	18.0	23.0	
	RSS(on)3	$I_S = 2.0\text{ A}$, $V_{GS} = 3.1\text{ V}$	13.5	19.0	26.5	
	RSS(on)4	$I_S = 2.0\text{ A}$, $V_{GS} = 2.5\text{ V}$	14.0	22.0	37.0	
Body Diode Forward Voltage	$V_{F(s-s)}$	$I_F = 2.0\text{ A}$, $V_{GS} = 0\text{ V}$		0.8	1.2	V
Input Capacitance ^{*1}	C_{iss}	$V_{SS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ kHz}$		910		pF
Output Capacitance ^{*1}	C_{oss}			105		
Reverse Transfer Capacitance ^{*1}	C_{rss}			80		
Turn-on Delay Time ^{*1,*2}	$t_d(\text{on})$	$V_{DD} = 10\text{ V}$, $V_{GS} = 0\text{ to }4\text{ V}$ $I_S = 2.0\text{ A}$		0.25		μs
Rise Time ^{*1,*2}	t_r			0.55		
Turn-off Delay Time ^{*1,*2}	$t_d(\text{off})$	$V_{DD} = 10\text{ V}$, $V_{GS} = 4\text{ to }0\text{ V}$ $I_S = 2.0\text{ A}$		1.65		μs
Fall Time ^{*1,*2}	t_f			1.0		
Total Gate Charge ^{*1}	Q_g	$V_{DD} = 10\text{ V}$		9		nC
Gate-source Charge ^{*1}	Q_{gs}	$V_{GS} = 0\text{ to }4\text{ V}$		2.6		
Gate-drain Charge ^{*1}	Q_{gd}	$I_S = 2.0\text{ A}$		2.4		

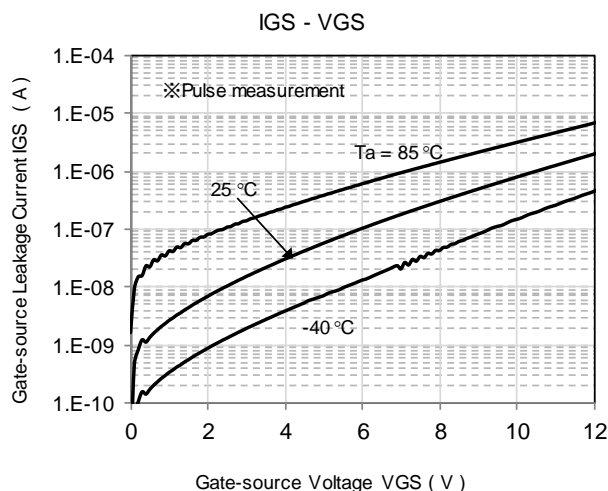
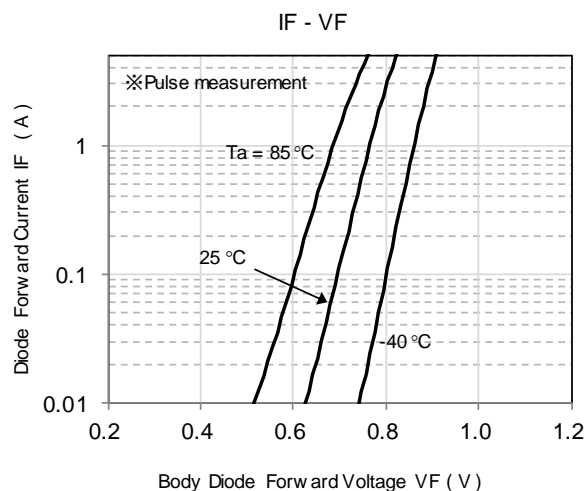
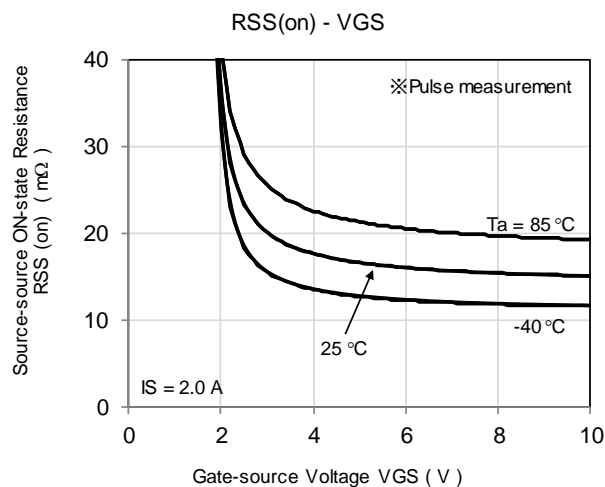
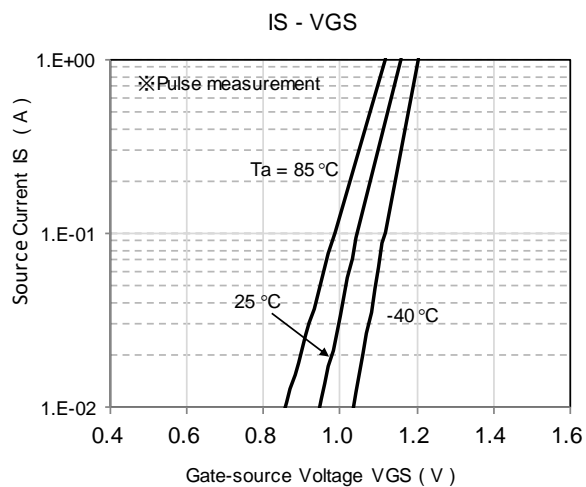
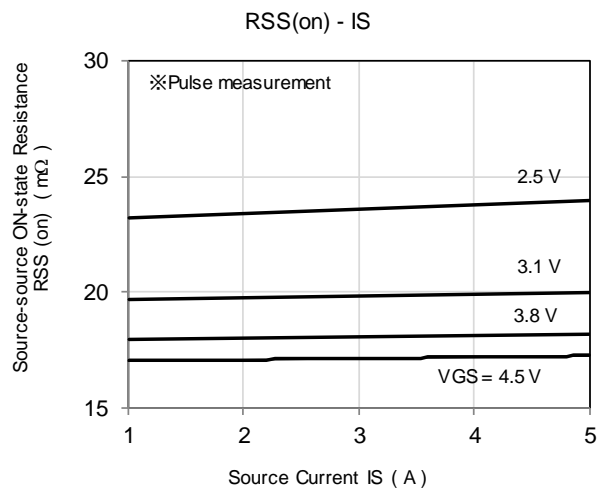
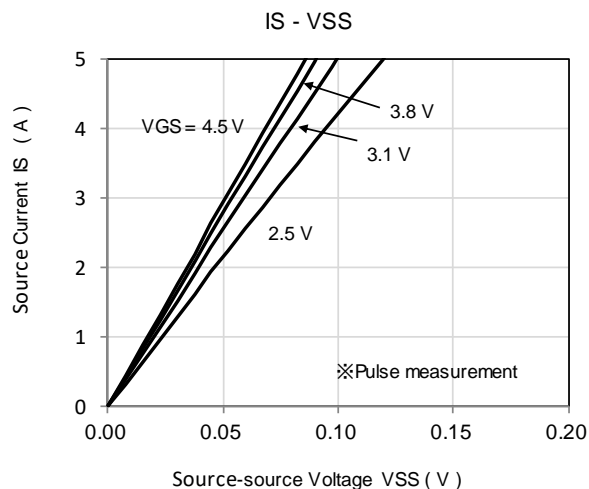
Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

*1 Guaranteed by design, not subject to production testing

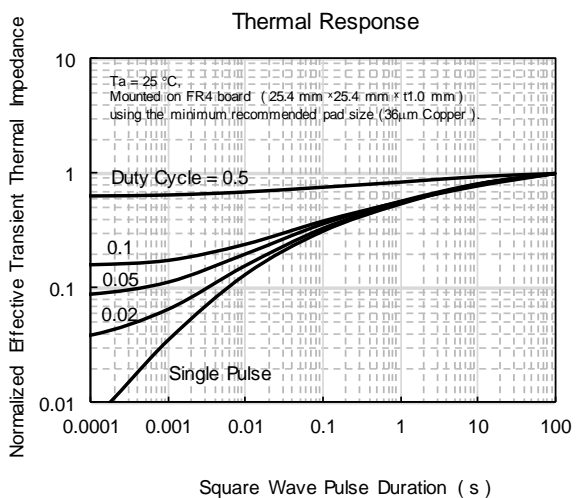
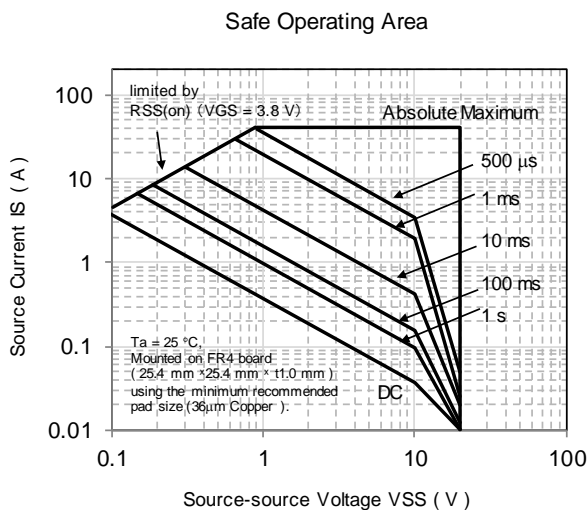
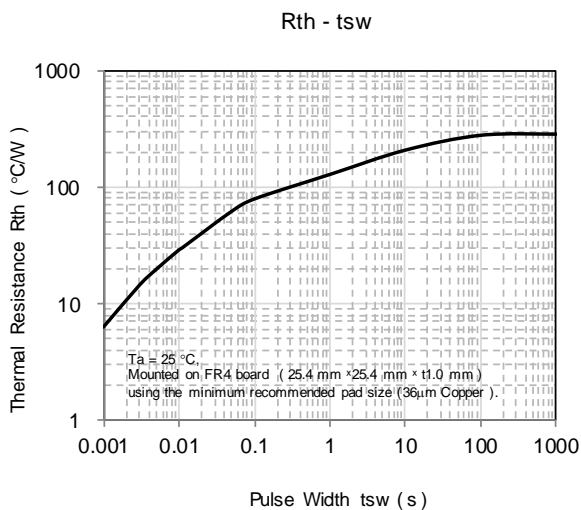
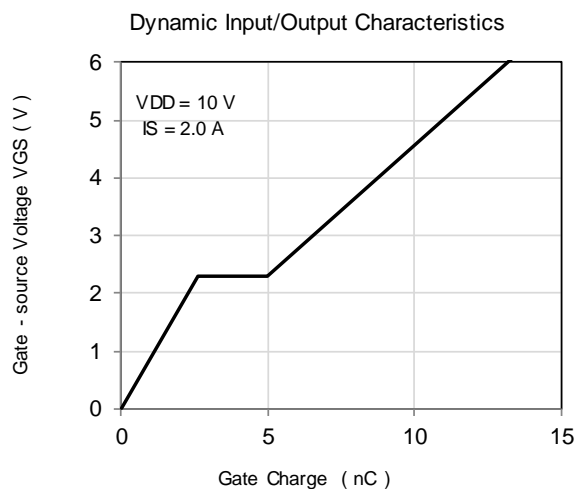
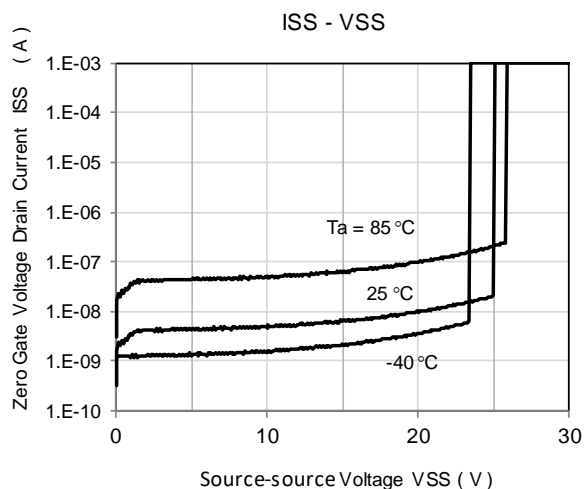
*2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



8. TECHNICAL DATA (Reference)

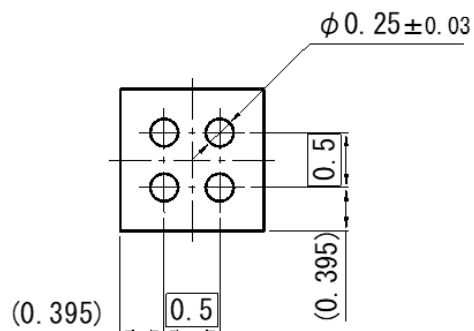
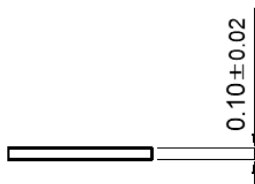
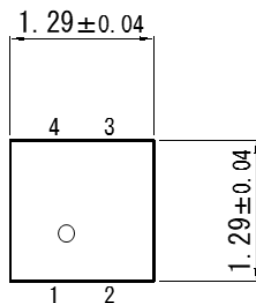


TECHNICAL DATA (Reference)



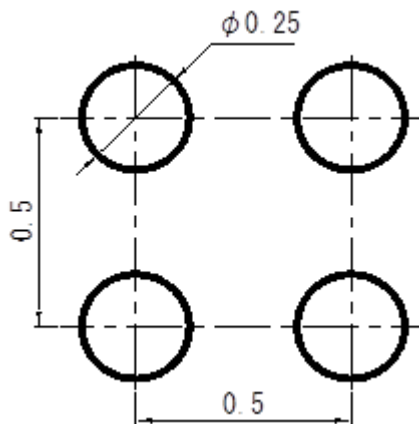
9. OUTLINE

Unit : mm



10. LAND PATTERN (Reference)

Unit: mm



12. REVISION HISTORY

Date	Revision	Description
2021.2.3	1.00	1. initially issued.

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